

Features:

- **RoHS Compliant**
- 150 Watts
- DC 2.7 GHz
- **AIN Ceramic**
- Non-Nichrome Resistive **Element**
- Low VSWR
- 100% Tester

Chip Attenuator 150 Watts, 30dB

Description:

The B150NA30X4 is a high performance Aluminum Nitride (AIN) chip attenuator intended as a cost competitive alternative to Beryllium Oxide (BeO). The attenuator is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators, and for use in power monitoring. The attenuator is also RoHS compliant!

General Specifications:

Resistive Element	Thick film
Substrate	AIN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-55 to +200°C (see de rating chart)

Electrical Specifications:

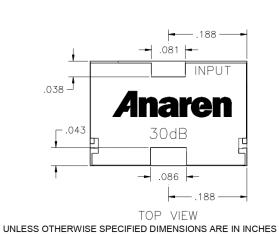
+0.5dB, -1dB DC-869 MHz **Attenuation Value:** 30dB ±0.5, 960MHz-2.3GHz +0.5, -1 dB, 2.2GHz-2.7GHz

Power: 150 Watts Frequency Range: DC - 2.7 GHz

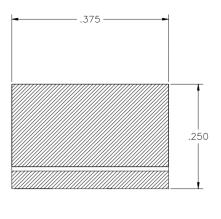
Input Return Loss: 20dB

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. Specifications subject to change.

Outline Drawing:



.040



SIDE VIEW

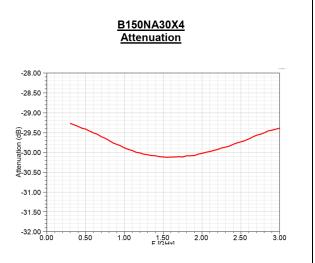
BOTTOM VIEW

Tolerance is ±0.010", unless otherwise specified. Designed to meet of exceed applicable portions of MIL-E-5400. All dimensions in inches.



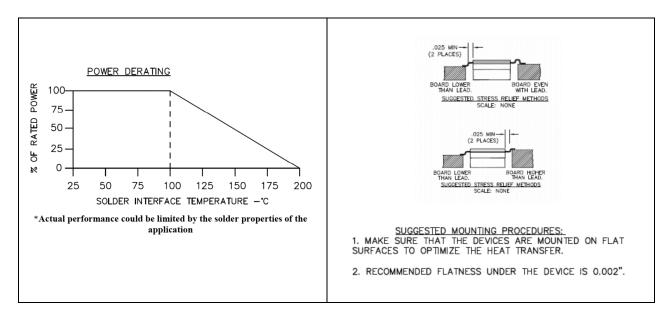
Typical Performance:





Power de-rating:

Mounting Footprint:



Contact us:

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